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集成微波光子滤波器研究进展(特邀)

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摘要:微波光子滤波器是一种将微波信号调制到光频域,并借助光电子器件在光域内对微波信号进行滤波的器件,相比于传统电学微波滤波器,其具有频率调谐范围大、频谱重构灵活以及抗电磁干扰等优势,在无线通信、雷达、电子战系统中具有广泛的应用前景。随着集成光电子技术的发展,微波光子滤波器也逐渐由分立光纤器件向集成化方向发展,以大幅减小体积、重量、功耗和成本。本文从集成微波光子滤波器的系统架构、工作原理以及性能出发,详细综述了非相干型和相干型集成微波光子滤波器的最新研究进展,分析了当前面临的技术难点与挑战,并对集成微波光子滤波器的未来发展趋势进行了展望。

关键词:微波光子;光电集成;微波光子滤波器;相干型滤波器;非相干型滤波器

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0 引言

微波滤波器是射频接收机前端的重要组成部分之一,通常用于在背景噪声中滤出目标微波信号或者有效抑制射频干扰信号,在无线通信、卫星通信、雷达、电子战系统中有着广泛的应用^[1]。传统的微波滤波器在电域内对射频信号进行滤波,但是还存在诸如缺乏可重构性、工作频率范围有限以及易受电磁干扰影响等缺点。微波光子滤波器通过将微波信号调制到光频域,并借助光电子器件在光域内对光载微波信号进行滤波,最后再通过光电转换到微波域。相比于传统微波滤波器,微波光子滤波器具有频率调谐范围大、频谱重构灵活以及抗电磁干扰等优势,成为微波光子技术领域的研究热点之一^[2]。经过几十年的发展,基于分立光纤器件构建的微波光子滤波器及其在通信、雷达、传感等领域已经得到了广泛研究^[3-5],但还存在体积大、重量重、功耗高、成本高、重构性能不足等问题,限制了其实用化,尤其在星载和机载这类对体积、功耗要求极高的应用场景。随着集成微波光子芯片技术的飞速发展,各类微波光子信号处理芯片也层出不穷^[6-9]。其中,集成微波光子滤波器也得到了广泛关注和研究,正在从仅在微波光子滤波链路中插入集成光学滤波器芯片,向激光器、调制器、光滤波器、光电探测器的全片上集成的方向发展^[1,10]。近年来,虽然已经有一些集成度较高的微波光子滤波器芯片相继报道,但是其综合性能、稳定性以及模块化封装离实用化还存在较大差距。本文从非相干和相干型集成微波光子滤波器的工作原理出发,综述了基于各类光学滤波器芯片的微波光子滤波技术及其集成化的研究进展,并在此基础上对集成微波光子滤波器的关键技术挑战进行了梳理,并对未来集成微波光子滤波器芯片技术的发展方向进行了展望。

1 集成微波光子滤波器简介

1.1 集成微波光子滤波器分类与工作原理

1.1.1 非相干型集成微波光子滤波器

按工作模式,集成微波光子滤波器通常可以分成非相干和相干型。其中,为了避免光学干涉,非相干型

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集成微波光子滤波器通常采用非相干光源或者多波长激光器阵列作为光源^[11],该类型微波光子滤波器通常采用抽头延迟线滤波器(Tapped Delay-Line Filters, TDLF)架构,根据抽头数量,可以分成有限脉冲响应(Finite Impulse Response, FIR)和无限脉冲响应(Infinite Impulse Response, IIR)滤波器。目前,非相干型集成微波光子滤波器主要采用FIR滤波器架构,其设计灵感源于基于离散信号处理算法的FIR数字滤波器,即输入信号被离散采样、延迟并加权后,再进行叠加,其数学形式为

$$H(\omega) = \sum_{n=0}^{N-1} a_n \cdot e^{-j\theta_n} \cdot e^{-jn\omega\Delta T} \quad (1)$$

式中, a_n 、 θ_n 和 ΔT 分别是第 n 个抽头采样的输入信号取样权重因子、第 n 个抽头采样信号的载波相移以及抽头采样信号间的时间延迟。由式(1)可以看出该类抽头延迟线滤波器的光谱响应具有周期性,其自由光谱范围(Free Spectral Range, FSR)由 $1/\Delta T$ 决定。如图1所示,通过将该抽头延迟线滤波器引入微波光子链路,即可实现微波光子滤波器。该类基于FIR型抽头延迟线的集成微波光子滤波器通常有两种实现方案,一种方案是在空域实现离散延时采样,多波长光源经调制、解复用后进入 n 个延时通道,采用不同长度的延时光波导(色散可忽略)对各波长信号进行多通道延迟,合波后再经光电探测器光电转换实现微波光子滤波,如图1(a)所示;另一种方案是在波长域实现离散延时采样,多波长光源经调制后进入色散器件,采用色散器件(如光子晶体波导)对各波长信号进行多通道延迟,再经光电探测器光电转换实现微波光子滤波,如图1(b)所示。非相干型微波光子滤波器可以通过选择抽头的个数、权重因子、延迟量实现对滤波带宽、频率和滤波谱形的调控,但是通常结构较为复杂。

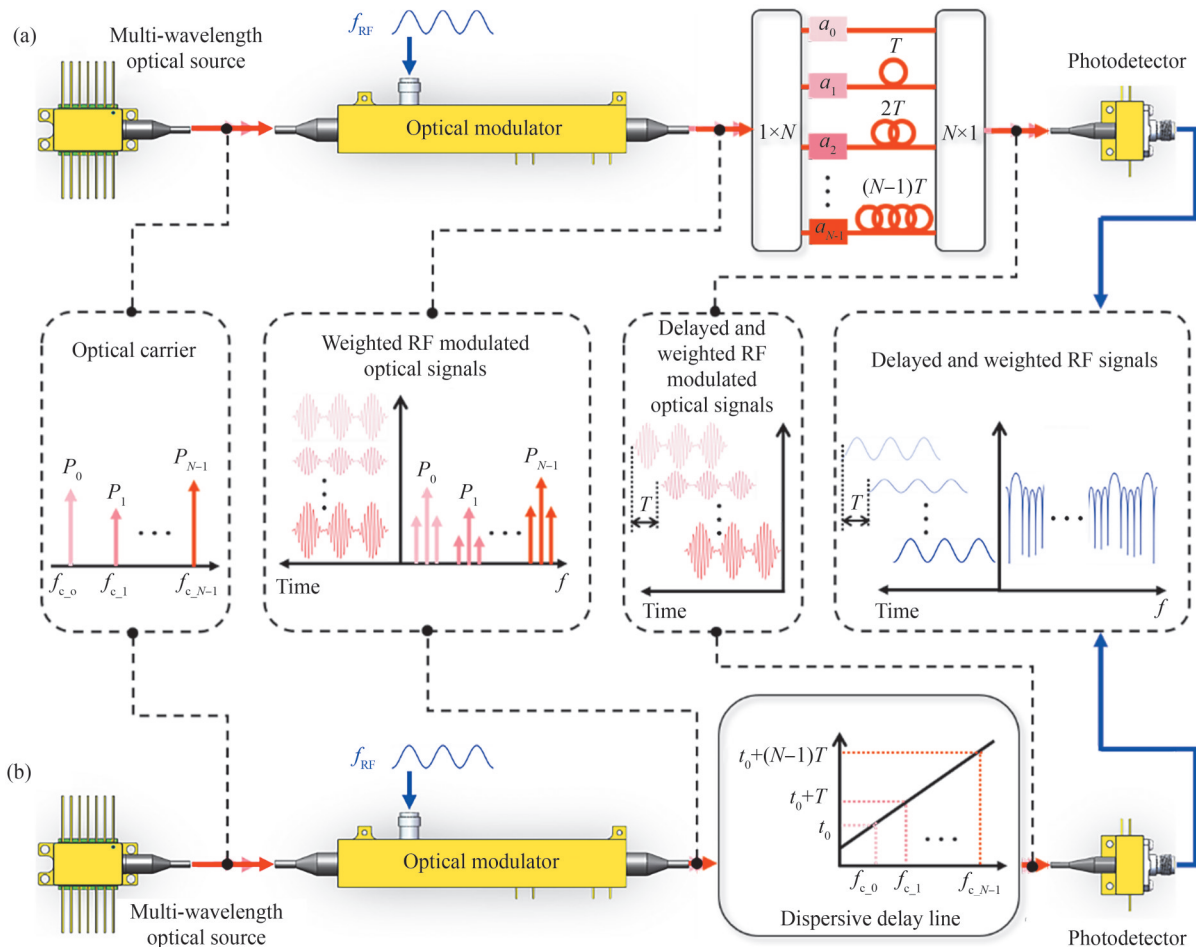


图1 非相干型微波光子滤波器链路架构。(a)基于多通道延迟光波导;(b)基于色散延迟器件

Fig. 1 Incoherent microwave photonic FIR filter link structure. (a) Based on multi-channel delay waveguides; (b) Based on dispersive delay components

1.1.2 相干型集成微波光子滤波器

与非相干型集成微波光子滤波器不同,相干型集成微波光子滤波器通常采用单波长激光器,通过电光调制器将待处理微波信号调制到激光载波上,然后借助于各种光学滤波器对该调制光信号的光边带和载波进行滤波处理,最后将处理后的光载波和光边带在光电探测器上拍频,实现光域滤波到微波滤波的转换,如图2所示。根据所引入的光学滤波器类型,也可以分成FIR和IIR型微波光子滤波器。其中,得益于IIR型滤波器无限抽头数,其可以实现高品质因子滤波器,从而提升滤波分辨率,如采用微环/微盘等构建的集成微波光子滤波器。相比非相干型集成微波光子滤波器,相干型集成微波光子滤波器的结构相对简单,且其微波滤波响应可以由调制格式和光学滤波器响应共同决定,因此具有更灵活的重构能力。

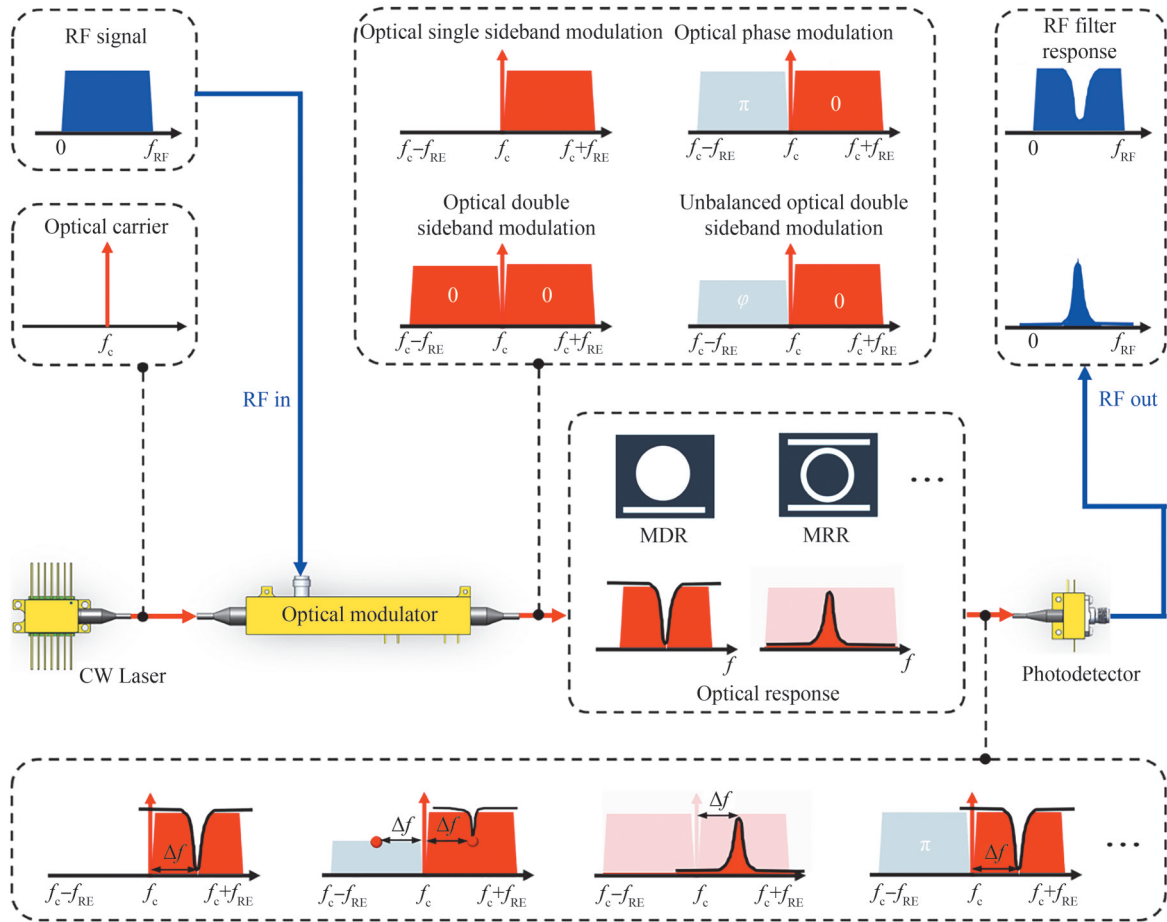


图2 相干型集成微波光子滤波器链路结构
Fig. 2 Coherent integrated microwave photonic filter link structure

2 集成微波光子滤波器研究进展

2.1 非相干型集成微波光子滤波器

对于非相干型集成微波光子滤波器,主要采用FIR滤波器架构,研究主要集中在基于色散延时采样的多抽头微波光子滤波器中所需的集成高色散芯片、多波长光源和光谱整形芯片。对于集成高色散芯片,西班牙瓦伦西亚理工大学的CAPMANY J课题组设计并制作了长度为1.5 mm的GaInP/GaAs光子晶体波导色散延时芯片,利用四个不同波长的激光器在其色散曲线上进行延迟离散采样,实现了四抽头的微波光子带阻滤波器,如图3所示^[12]。

基于色散延时采样的多抽头微波光子滤波器通常需要多个不同波长的激光光源,这将大大增加系统成本和体积。而集成光频梳芯片可以解决该问题,普渡大学的WEINER A M等采用氮化硅微环光频梳中的21根光梳齿作为多波长光源,结合长度为1.8 km的单模光纤作为色散元件,实现了21抽头的微波光子带通滤波器,如图4(a)所示,微波光子带通滤波器的带宽和射频带外抑制分别为1.1 GHz和~25 dB,频率调谐范

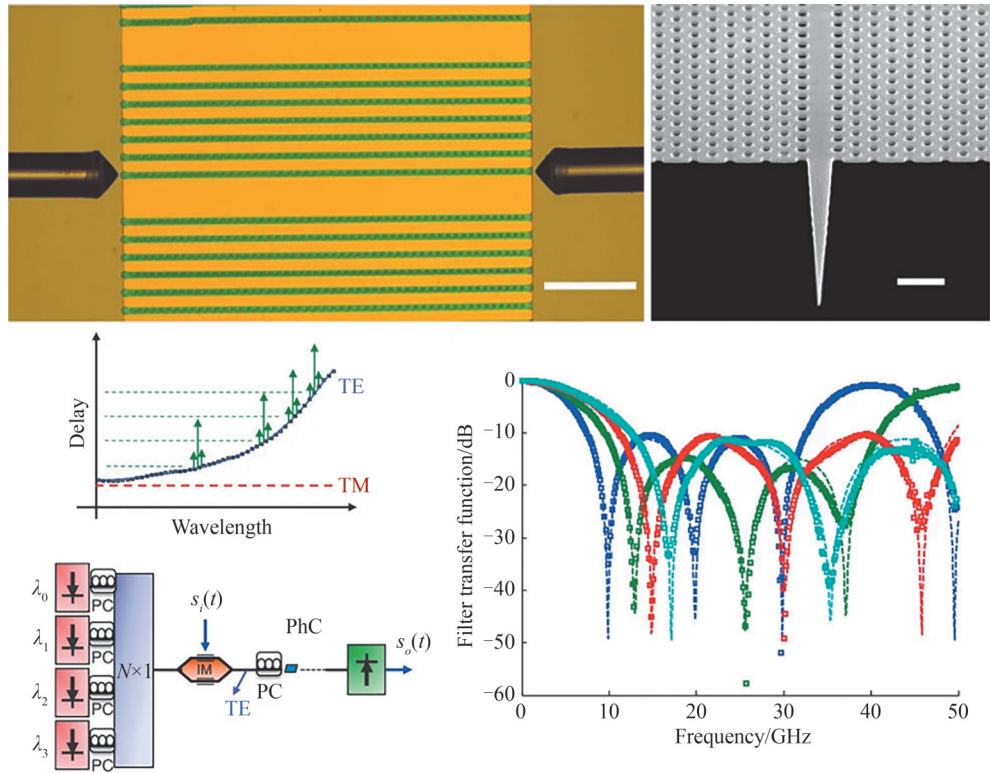


图3 基于光子晶体波导延时芯片的四抽头微波光子带阻滤波器^[12]

Fig. 3 A four-tap microwave photonic band-stop filter based on a photonic crystal waveguide delay chip^[12]

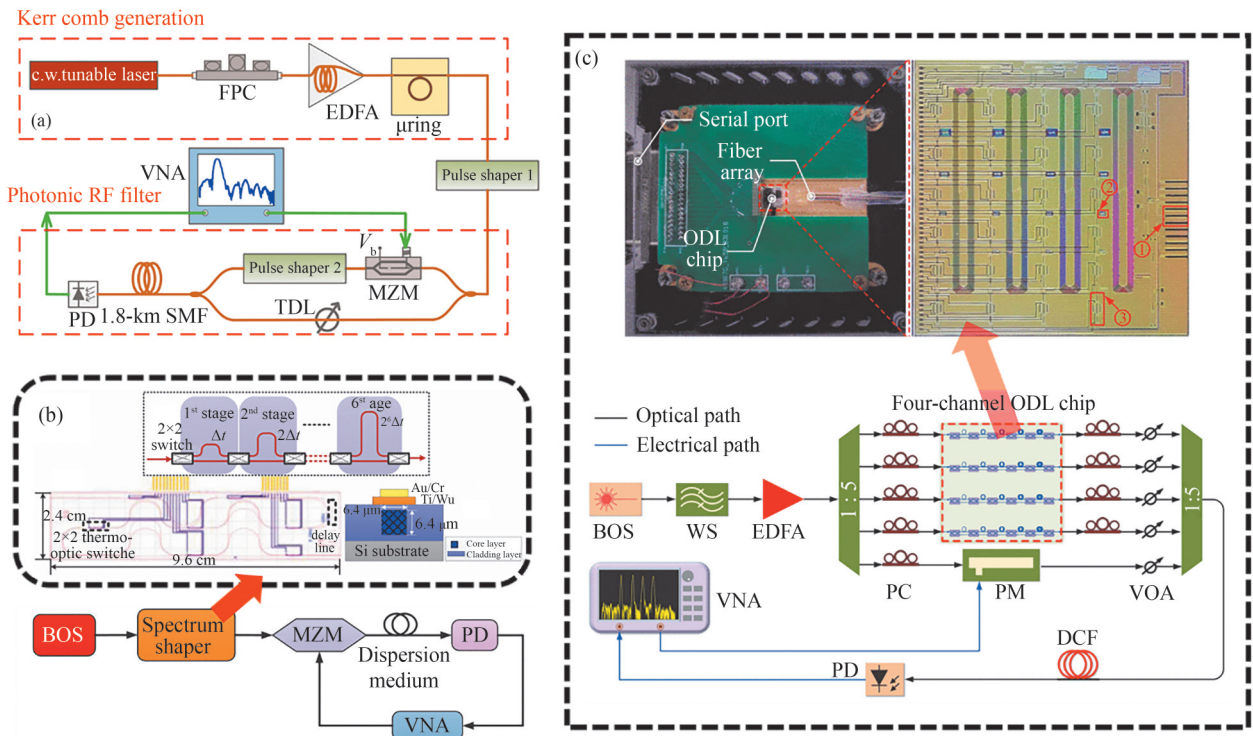


图4 基于集成光芯片的非相干型微波光子带通滤波器。(a)基于集成 Si_3N_4 微环光频梳芯片^[13]；(b)基于 SiO_2 光谱整形芯片^[14]；(c)基于SOI光谱整形芯片^[15]

Fig. 4 Incoherent microwave photonic band-pass filters based on integrated photonic chips. (a) Based on an integrated Si_3N_4 micro-ring chip^[13]；(b) Based on a SiO_2 spectral shaping chip^[14]；(c) Based on an SOI spectral shaping chip^[15]

围 2.5~17.5 GHz^[13]。除了采用多通道激光源,也可以采用宽带光源加光谱整形器来实现多抽头微波光子滤波器,中科院半导体所的李明课题组将 6 bit 的 SiO₂ 开关延时线芯片设置在非开关状态,利用其干涉光谱对宽带光源进行光谱整形,整形后的光谱作为多波长光源,结合色散补偿光纤搭建了微波光子带通滤波器,如图 4(b) 所示,微波光子带通滤波器的频率可以在 1~12 GHz 内离散切换,射频带外抑制约 35 dB,带宽约 240~600 MHz^[14]。为了进一步提高集成度和滤波通道数,北京理工大学的张伟锋课题组采用四通道 5 bit 的硅基开关延时线芯片对宽带光源进行光谱整形,结合色散补偿光纤等光纤器件构建了四通道的带通微波光子带通滤波器,如图 4(c) 所示,滤波器带宽 156 MHz,频率调谐范围 24 GHz,射频带外抑制比 30 dB,且四个微波光子滤波通道的独立开关控制^[15]。

以上基于集成器件的非相干型微波光子滤波器对比如表 1 所示,可以看出该类滤波器可以实现频率调谐和较好的带外抑制,但是滤波带宽调谐范围相对较小。其滤波带宽受到延迟抽头数量的限制,要实现高频率分辨率的微波光子滤波需要增加延迟抽头数,无论采用多波长激光器阵列还是宽带光源光谱整形的方案,其设计、制作和调控难度都比较大,成本也相对较高;另一方面,通常该类滤波器的带宽和频率难以实现独立调谐,即频率调谐过程中往往伴随着带宽的变化;此外,片上还难以实现复数抽头系数,限制了其微波滤波器频谱重构能力。此外,目前仅局限于将光谱整形芯片、多波长源等单元器件引入微波光子滤波器链路,其他器件主要还是采用分立光纤器件,更高集成度的该类微波光子滤波器还未见报道。

表 1 基于集成器件的非相干型微波光子滤波器性能

Table 1 Performance of incoherent microwave photonic filter based on integrated components

Microwave photonic filter scheme	Filter type	Filter bandwidth/ GHz	Frequency tuning range /GHz	Out-of-band suppression /dB
Photonic crystal waveguide + laser array ^[12]	Band-pass/ Band-stop	8/1~2	>40	10/50
Si ₃ N ₄ micro-ring based optical frequency comb + single-mode fiber dispersion ^[13]	Band-pass	1.1	2.5~17.5	25
Spectral shaping chip + DCF fiber dispersion ^[14]	Band-pass	0.24~0.6	1~12	35
Spectral shaping chip + DCF fiber dispersion ^[15]	Band-pass	0.156	0.8~24	30

2.2 相干型集成微波光子滤波器

2.2.1 基于微环/微盘的微波光子滤波器

微环和微盘光学谐振腔滤波器以其结构简单、易于调谐的优点,被广泛用于构建各种带阻、带通以及带阻/带通切换型微波光子滤波器。

1) 微波光子带阻滤波器

基于微环/微盘实现微波光子带阻滤波器,其最直接的实现方案就是采用光学单边带(Optical Single Sideband, OSSB)调制如图 5 所示。该方案可以将微环/微盘滤波器的光学带阻滤波响应一一映射到微波

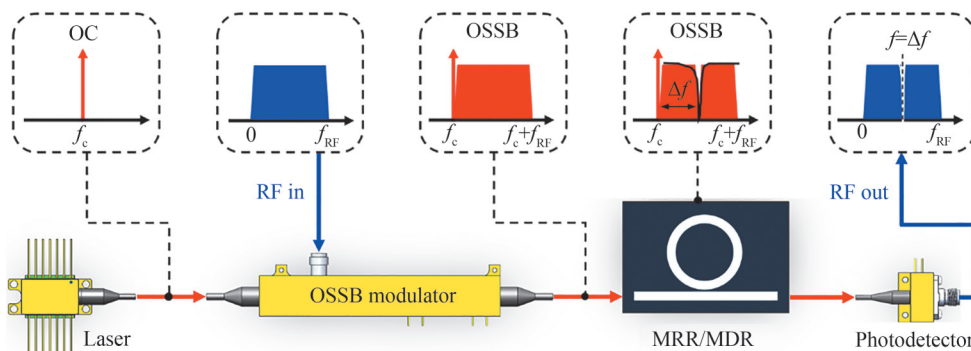


图 5 基于微环/微盘和光学单边带调制的微波光子带阻滤波器链路示意图

Fig. 5 Schematic diagram of a microwave photonic band-stop filter link based on micro-ring / micro-disk and optical single-sideband modulation

域,因此其微波滤波频谱完全取决于微环/微盘的光学滤波频谱,且通过调谐光载波与微环/微盘共振波长间隔可以实现微波光子带阻滤波器频率调谐,频率调谐范围通常为微环/微盘自由光谱范围(Free Spectra Range, FSR)的一半。但是,通常制作的微环/微盘光学带阻滤波器的消光比有限(一般20~30 dB),一一映射到微波域后难以满足高射频抑制比的微波滤波需求。

为了解决该问题,悉尼大学的MARPAUNG D等在2013年提出了一种基于非平衡光学双边带(Unbalanced Optical Double Sideband, UODS)调制的射频相消技术,结合双平行调制器和高品质因子(Quality Factor, Q)氮化硅全通型微环滤波器,构建了超高射频抑制的微波光子带阻滤波器,如图6(a)所示,通过调控双驱动/双平行调制器调控非平衡OSDB调制产生的两个光边带的振幅比,使振幅大的光边带经微环带阻滤波后,在滤波中心频率处的振幅与振幅小的光边带一致,再结合“过耦合”微环在滤波中心频率处的 π 相移,使滤波中心频率处满足振幅相等、相位相反的干涉相消条件,从而在微波域实现射频相消,进而突破微环光学滤波器的消光比限制,达到射频抑制 >60 dB,带宽调谐范围247~840 MHz,频率调谐范围2~8 GHz^[16]。在此基础上,我们进一步验证了“过耦合”和“欠耦合”微环,都可以结合双驱动/双平行调制器实现射频干涉相消,不但可以实现超高射频抑制比,还可以增大微波光子带阻滤波器的带宽调谐范围,达到了0.65~2.2 GHz^[17]。为了摆脱复杂的双驱动/双平行调制器,悉尼大学的LIU Yang等人进一步提出了分别采用一个“过耦合”和一个“欠耦合”微环分别处理MZM强度调制产生的上下两个光边带的方案,调谐两个微环的消光比一致并利用“过耦合”和“欠耦合”微环在共振波长处分别为 π 和0相位,同样实现了射频相消,如图6(b)所示^[18],并且进一步结合MZM调制器低偏、多级光放大实现了净射频增益、噪声系数 <20 dB、SFDR = 115 dB·Hz^{2/3},以及射频抑制 >50 dB的微波光子带阻滤波器^[19]。以上方案中微环对振幅和相位的调控是相互影响的,因此在微波域实现振幅相等、相位相反的调控难度较大。为了解决该问题,华中科技大学张新亮课题组采用两个MZI级联一个全通SOI微环滤波器,将射频相消链路中的振幅和相位调控在空间上分离,也实现了超高射频抑制^[20]。为了进一步提高集成度,最近MARPAUNG D课题组在薄膜铌酸锂(Thin Film Lithium Niobate, TFLN)材料平台上,通过单片集成一个强度调制器和四个级联可调微环,采用一对“过耦合”和“欠耦合”微环分别对上下边带滤波,同时采用另一个“过耦合微环”对光载波进行剪裁,报

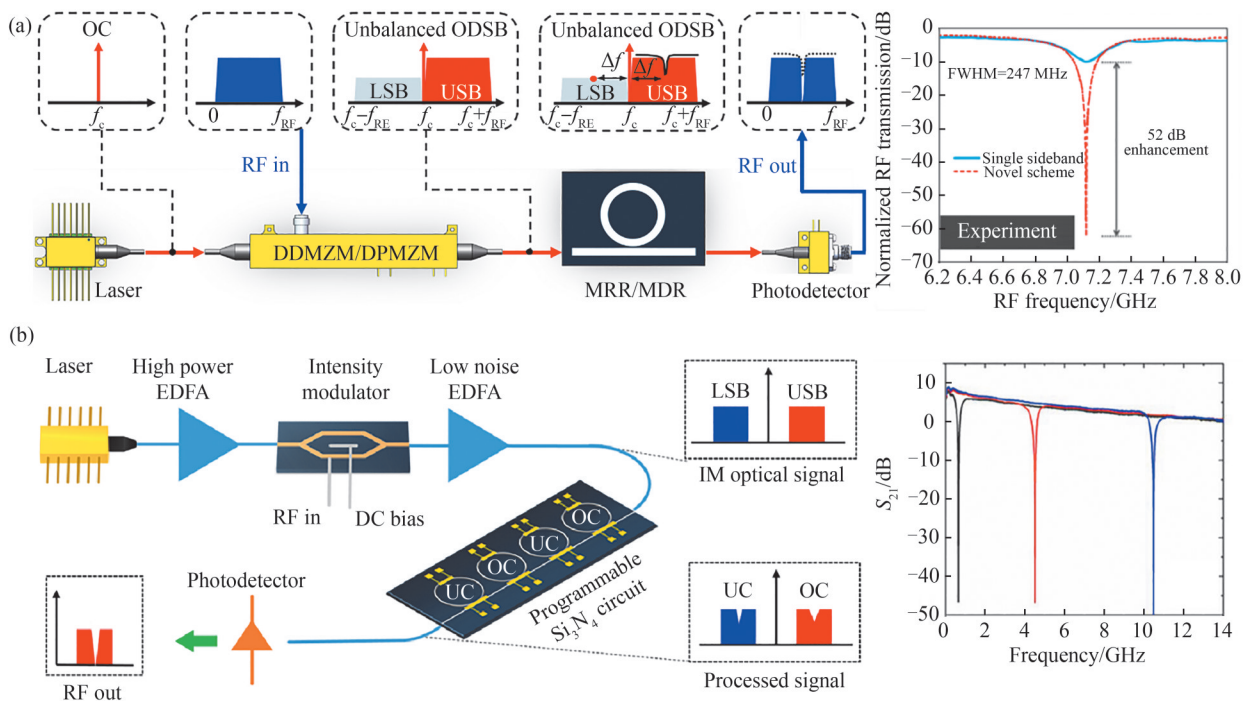


图6 基于射频干涉相消技术的超高射频抑制微波光子带阻滤波器。(a)采用双驱动/双平行调制器和单个微环^[17]; (b)采用强度调制器和级联微环^[18]

Fig. 6 Ultra-high RF suppression microwave photonic band-stop filter based on radio frequency interference cancellation technology. (a) Adopting dual-drive/dual-parallel modulator and a single micro-ring^[17]; (b) Adopting intensity modulator and cascaded micro-rings^[18]

道了一款可调谐微波光子带阻滤波器^[21],频率调谐范围 1.5~21.5 GHz,射频抑制比超过 60 dB,滤波带宽约 1.3 GHz, SFDR = 110 dB·Hz^{2/3}。

2) 微波光子带通滤波器

基于微环/微盘实现微波光子带通滤波器,一种最直接有效的实现方案就是通过“光载波分离再入”技术将 Add-Drop 型微环/微盘的光学带通滤波频谱从光域直接一一映射到微波域,如图 7 所示。将光载波分成两束,其中一束经调制器调制后进入 Add-Drop 型微环/微盘进行带通滤波,经滤波后的光载微波信号再与另一束光载波信号在光电探测器上拍频实现光域到微波域的滤波频谱映射。该方案实现的微波光子带通滤波器的带宽和射频带外抑制完全取决于 Add-Drop 型微环/微盘的光学带宽和消光比,滤波器的频率调谐则可以通过改变光载波与微环/微盘共振波长间隔实现。

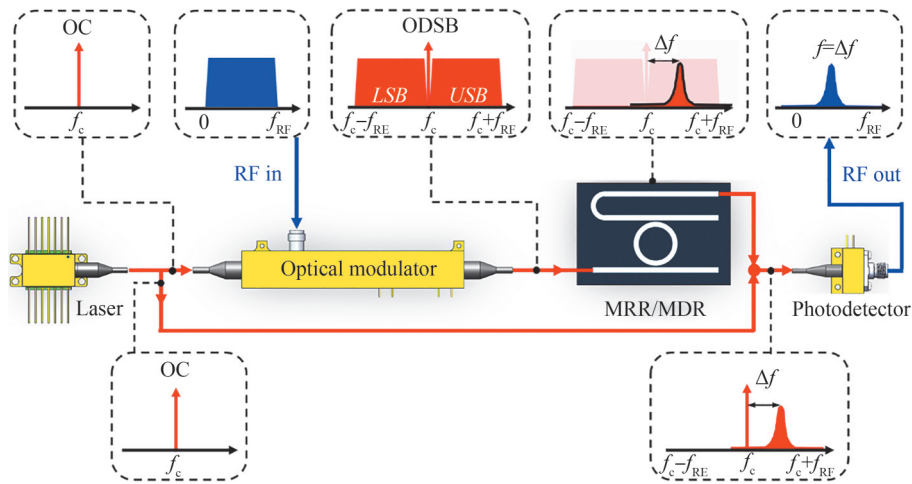


图 7 基于微环/微盘光域-微波域频谱映射的微波光子带通滤波器链路示意图

Fig. 7 Schematic diagram of a microwave photonic band-pass filter link based on optical-microwave domain spectral mapping of micro-ring/micro-disk

2016年,清华大学的陈明华课题组采用单个高Q值可调谐氮化硅 Add-Drop 微环,结合“光载波分离再入”技术,构建了可调谐微波光子带通滤波器,如图 8(a)所示,带宽约 420 MHz,射频带外抑制约 44 dB,频率调谐范围 1~40 GHz^[22]。但由于采用的微环带宽不可调,因此无法实现微波光子滤波器带宽调谐,接近洛伦兹形的滤波频谱的形状因子也有限。为了解决该问题,华中科技大学张新亮课题组采用四级联可调微环构成的硅基耦合谐振器光波导(Coupled Resonator Optical Waveguides, CROW)带通滤波器,结合“光载波分离再入”技术报道了频率和带宽可调谐微波光子带通滤波器,如图 8(b)所示。得益于高阶 CROW 优异的光谱形状因子和消光比,实现了高达 32~42 dB 射频带外抑制和约 10 dB/GHz 的射频滚降率,且微波光子滤波器的频率和带宽调谐范围分别达到 4~36 GHz 和 0.24~1.76 GHz^[23]。

虽然“光载波分离再入”可以实现光学带通滤波频谱的光域-微波域映射,但是存在链路复杂、滤波频谱调控手段完全依赖光学滤波器的不足。因此,另一种基于“相位-强度转换”链路的微波光子带通滤波器架构被广泛采用,如图 9 所示。光载波经相位调制后产生两个振幅相等、相位相反的两个光边带,这两个光边带在光电探测器上与光载波拍频完全射频相消,若采用全通型微环/微盘带阻滤波器滤除其中一个光边带,可以破坏射频相消条件实现“相位-强度转换”,进而实现微波光子带通滤波。

提高频率分辨率是微波光子滤波器的一个重要研究方向,由于基于微环/微盘的微波光子滤波器带宽主要取决于微环/微盘的光学带宽,因此提高微环/微盘的 Q 值成为提高微波光子滤波器频率分辨率的最有效手段。通过在宽度增大的多模光波导中传输基模,可以有效抑制微环制作过程中光波导侧壁粗糙度引起的散射损耗,从而提高微环 Q 值并减小带宽。华中科技大学董建绩课题组采用多模 SOI 光波导和单模弯曲波导构建的低损耗 Add-Drop 型微环($Q \sim 1.14 \times 10^6$),结合相位调制链路构建了可调谐微波光子带通滤波器,如图 10(a)所示。滤波器的带宽约 170 MHz,射频带外抑制 26.5 dB,频率调谐范围 2~18.4 GHz^[24]。浙江大学戴道锌课题组进一步通过采用全多模 SOI 光波导构建的低损耗全通型微环($Q \sim 0.94 \times 10^7$),结合相位

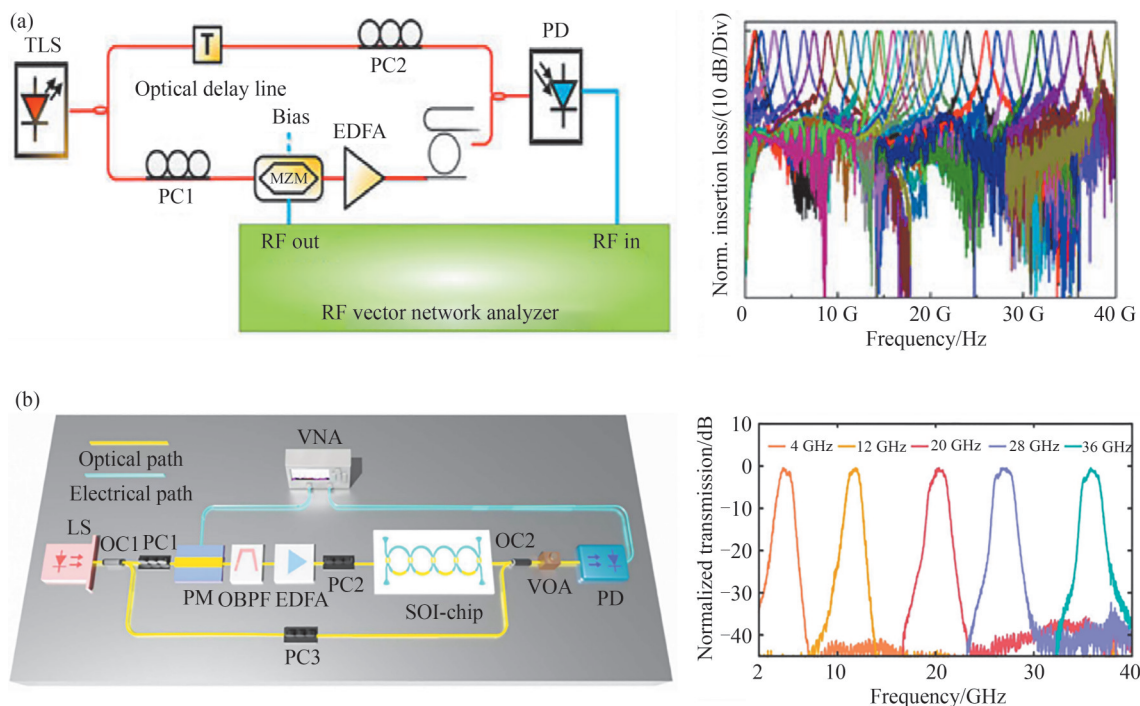


图8 采用“光载波分离再入”技术的微波光子带通滤波器。(a)基于单个 Add-Drop 微环^[22]；(b)基于 CROW^[23]
 Fig. 8 Microwave photonic band-pass filters based on “optical carrier separation and reentry” technology. (a) Based on a single Add-Drop micro-ring^[22]；(b) Based on a CROW^[23]

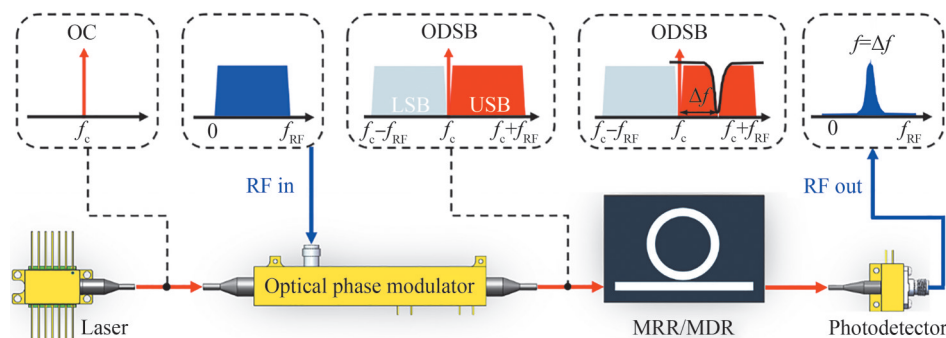


图9 基于“相位-强度转换”和微环/微盘的微波光子带通滤波器链路示意图

Fig. 9 Schematic diagram of a microwave photonic band-pass filter link based on “phase-intensity conversion” and micro-rings/micro-disks

调制链路实现了带宽仅有 20.6 MHz 的微波光子带通滤波器,如图 10(b)所示。滤波器的射频带外抑制 26.5 dB,频率调谐范围 3.4~19.3 GHz^[25]。相比微环的两个波导侧壁,微盘由于只有一个侧壁,原理上具有更低的散射损耗,因此一些基于微盘的窄带微波光子带通滤波器也相继报道。北京理工大学的张伟锋课题组采用高 Q 值 SOI 微盘滤波器,结合相位调制实现了滤波器带宽约为 103 MHz 的微波光子带通滤波器^[26],如图 10(c)所示。我们也采用高 Q 值 Si₃N₄ 微盘结合相位调制实现了带宽约为 63 MHz 的微波光子带通滤波器^[27],如图 10(d)所示。

另一方面,基于单个微环/微盘和相位调制实现的微波光子带通滤波器的频谱形状是类洛伦兹形,而且当滤波器频率接近微环/微盘的 FSR/2 时,由于相邻 FSR 谐振的残余相位影响会导致非对称的频谱,进而恶化微波光子带通滤波器的射频带外抑制和形状因子。为了解决该问题,可以采用级联微环分别处理相位调制的两个光边带并进行拍频,从而在微波域进行频谱调控。悉尼大学的 SONG Shijie 等将光载波置于两个带宽不同的级联“欠耦合”SOI 微环谐振波长之间,结合相位调制链路,实现了频谱形状因子 1.78、频率调谐范围 6~17 GHz、射频带外抑制约 20 dB 的微波光子带通滤波器^[28]；我们采用两个耦合系数可调谐的级联

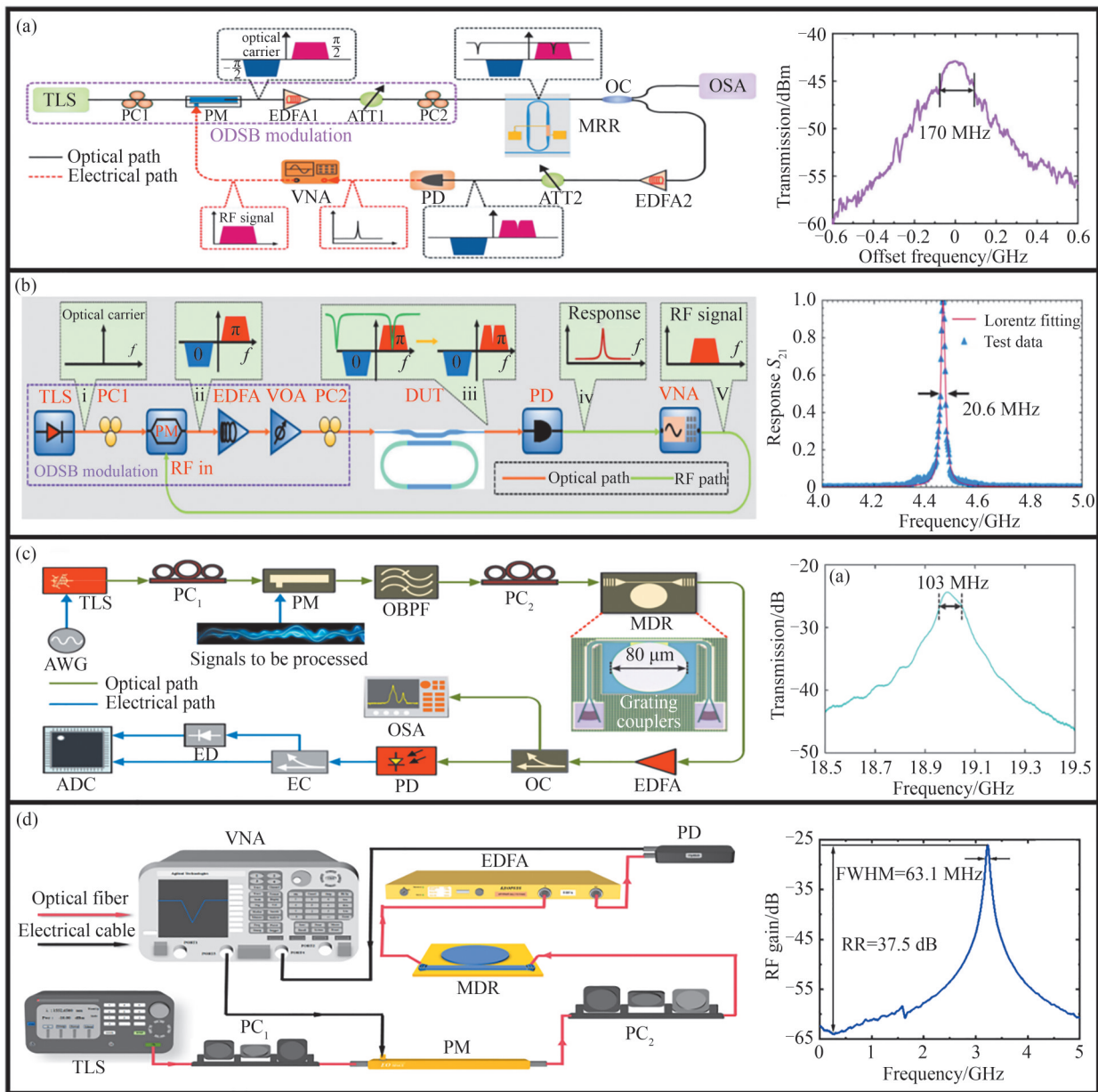


图 10 基于高 Q 值微环/微盘的微波光子带通滤波器。(a)采用基于部分多模波导的 SOI 微环^[24]; (b)采用基于全多模波导的 SOI 微环^[25]; (c)采用 SOI 微盘^[26]; (d)采用 Si_3N_4 微盘^[27]
 Fig. 10 Microwave photonic band-pass filters based on high-Q micro-ring/micro-disk. (a) Adopting a SOI micro-ring based on partially multimode waveguide^[24]; (b) Adopting a SOI micro-ring based on fully multimode waveguide^[25]; (c) Adopting a SOI micro-disk^[26]; (d) Adopting a Si_3N_4 micro-disk^[27]

Si_3N_4 微环,通过精确匹配两个微环消光比和带宽,进一步将微波光子带通滤波频谱形状因子和带外抑制优化至 1.23 和 34 dB^[29]。此外,这种结合级联微环和相位调制构建微波光子带通滤波器的方案,在改进滤波形状因子的同时还能实现大范围的滤波带宽动态重构^[29-32]。为了进一步提升微波光子滤波器的重构能力,还可以通过采用双驱动/双平行调制器实现等效相位调制和非平衡双边带调制^[17],进而实现微波光子带通/带阻滤波器的动态切换^[33-35];或者通过在片上增加额外的光谱整形和幅/相调控器件对双边带调制光信号进行剪裁,从而实现微波光子带通/带阻滤波器的动态切换^[36, 37]。

对于该类基于微环/微盘的微波光子滤波器,其优点是其结构和制作工艺相对简单,能通过级联方式提高滤波器射频带外抑制、带宽调谐范围等性能,还能够与调制器、探测器等器件进行单片集成;其不足是其有限的 FSR 限制了微波光子滤波器的频率调谐范围,且其较高的温度敏感性对构建的微波光子滤波器的频率稳定性和控制提出了较高的挑战。

2.2.2 基于波导受激布里渊散射效应的微波光子滤波器

由于声子寿命较长,基于三阶非线性声光相互作用的受激布里渊散射(Stimulated Brillouin Scattering, SBS)可以实现固有带宽非常窄(约几十 MHz)的SBS增益谱和SBS损耗谱,且不存在自由光谱范围FSR,因此不会对所构建的微波光子滤波器的工作频率调谐范围造成任何限制。且得益于 As_2S_3 玻璃材料的高弹光系数以及 As_2S_3 波导对声波和光波模式的高重叠度,其可在紧凑的尺寸内实现高SBS增益。悉尼大学的EGGLETON B J课题组在该领域报道了一系列研究工作。2012年,他们首次提出采用 As_2S_3 光波导SBS增益谱结合相位调制链路构建超窄带的微波光子带通滤波器,滤波器带宽约23 MHz,如图11(a)所示^[38];2015年,他们又基于 As_2S_3 光波导的SBS增益谱或损耗谱,结合非平衡双边带调制实现射频相消,报道了带宽33 MHz、射频抑制 >55 dB的超窄带、超高射频抑制微波光子带阻滤波器,如图11(b)所示^[39];为了克服基于单个SBS增益/损耗谱构建的微波光子滤波器无法实现滤波器带宽调谐的不足,2016年,他们又进一步通过引入多个泵浦光调控并拓宽 As_2S_3 光波导的SBS增益谱,结合相位调制链路实现了带宽可调的微波光子带通滤波器,实现了30~440 MHz的滤波器带宽调谐^[40];还通过利用 As_2S_3 光波导的SBS增益和损耗谱同时对相位调制光信号进行频谱整形,构建了带宽和频率可调谐的微波光子带通滤波器^[41]。

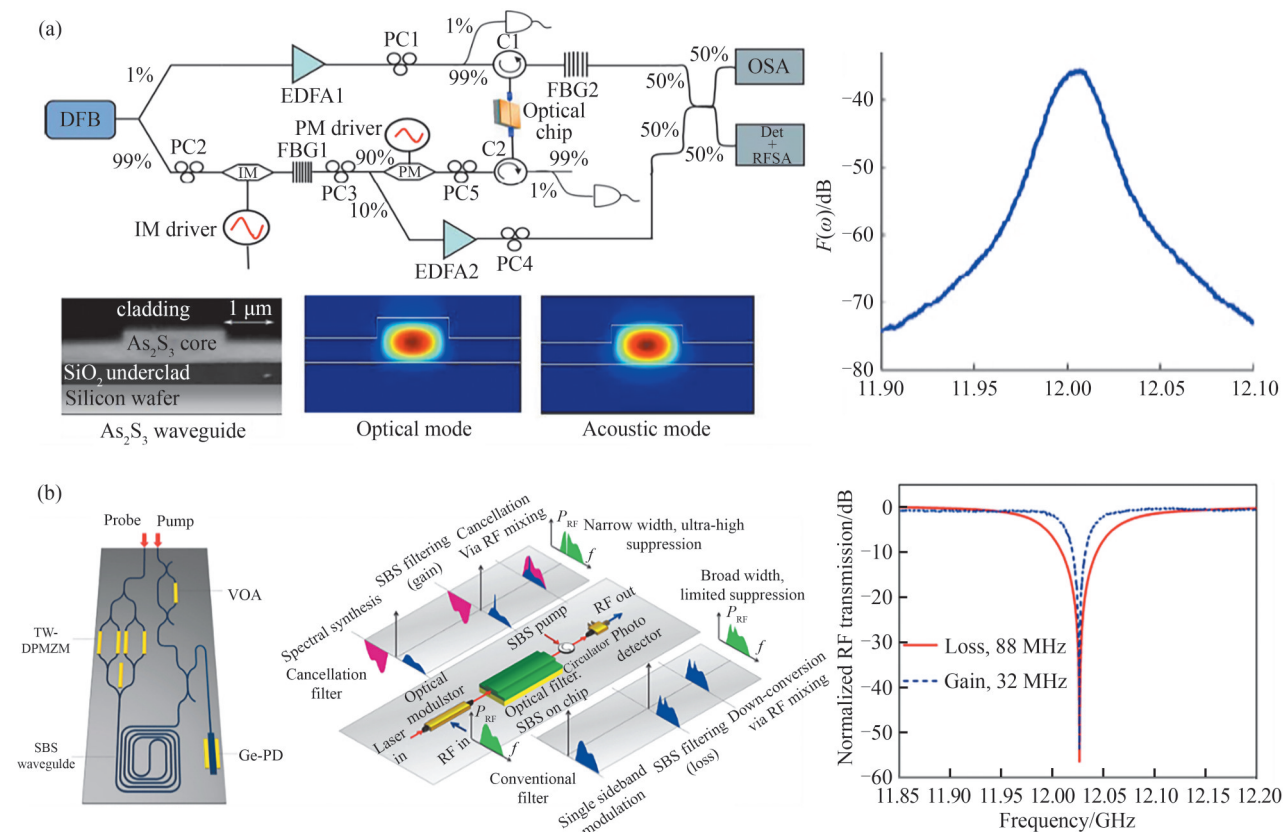


图11 基于 As_2S_3 波导SBS效应的微波光子滤波器。(a)带通滤波器^[38]; (b)带阻滤波器^[39]

Fig. 11 Microwave photonic filter based on SBS effect in As_2S_3 waveguide. (a) Band-pass filter^[38]; (b) Band-stop filter^[39]

对于该类基于非线性光波导SBS效应的微波光子滤波器,其最大的优势是可以实现低至20~30 MHz的超窄滤波器带宽,且其不存在FSR的特性可以支持非常大的频率调谐范围。但是,其缺点是通常需要额外提供很高功率的泵浦光,导致滤波器的链路相对复杂;另外,其带宽调谐能力也十分有限。

2.2.3 基于其他集成光器件的微波光子滤波器

此外,还有一些基于其他集成光器件的微波光子滤波器报道。华中科技大学董建绩组采用SOI光子晶体微腔,结合非平衡双边带调制技术,实现了射频抑制比和频率可调的微波光子带阻滤波器^[42],如图12(a)所示,但光子晶体需要很高的加工精度;2019年,暨南大学的YU Bei等采用光纤倏逝场耦合的高Q值 SiO_2 微球,结合非平衡双边带调制技术,实现了带宽15 MHz的超窄带、高射频抑制比微波光子带阻滤波器^[43],如图12(b)所

示,但其无法实现片上集成;意大利 TeCIP 研究所 PORZI C 等通过单片集成相位调制器、四阶级联相移波导布拉格光栅滤波器、光电探测器等,构建了带宽调谐范围 5~10 GHz 的硅基可调谐微波光子带通滤波器^[44],如图 12(c)所示,但相移波导光栅很难实现亚 GHz 带宽,且也需要高加工精度;以色列巴伊兰大学的 KATZMAN M 等通过激发悬空硅波导上的声表面波(Surface Acoustic Wave, SAW),构建了滤波带宽约为 5 MHz 的超窄带微波光子带通滤波器^[45],如图 12(d)所示,但其 FSR 仅有 65 MHz,且微波光子滤波器的频率不可调,需要非常高的微波功率激发出 SAW,还需要多个高功率激光源,系统链路非常复杂。

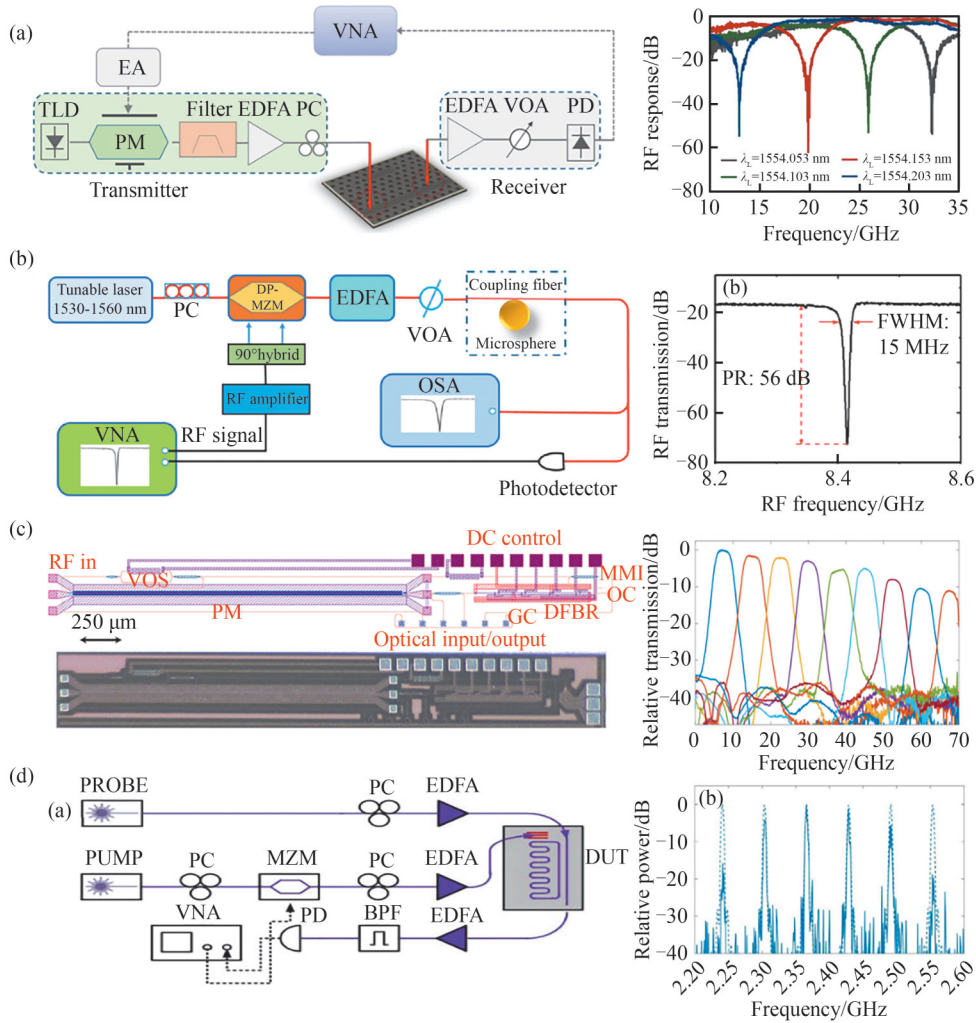


图 12 基于其他集成光器件的微波光子滤波器。(a)采用硅基光子晶体微腔^[42]; (b)采用 SiO₂微球^[43]; (c)采用硅基相移波导光栅^[44]; (d)采用悬空硅波导的声表面波 SAW^[45]

Fig. 12 Microwave photonic filters based on other integrated optical components. (a) Adopting a silicon photonic crystal microcavities^[42]; (b) Adopting a SiO₂ microsphere^[43]; (c) Adopting a silicon phase-shift waveguide gratings^[44]; (d) Adopting surface acoustic wave in suspended silicon waveguide^[45]

2.2.4 高集成度微波光子滤波器芯片

随着光电集成技术的发展,在微波光子信号处理芯片集成化、小型化应用需求的牵引下,微波光子滤波器也正在通过各种片上集成技术手段将光源、调制器、滤波器、探测器等进行异质/异构集成,从而大大减小微波光子滤波器的体积和功耗,并提高稳定性。其中, TFLN 材料平台以其优异的宽带电光调制特性,可以支持大频率调谐范围的微波光子滤波器^[21, 46, 47], 2025 年, MARPAUNG D 课题组在 LNOI 平台上,通过级联一个薄膜铌酸锂强度调制器和四个级联可调微环谐振器,研发出一款大动态范围、高链路增益、低噪声系数和超高抑制度的可调谐微波光子带阻滤波器^[21],如图 13(a)所示。同年,国内浙江大学戴道铎^[46]和储涛^[47]课题组也分别报道了单片集成电光调制器和微环的微波光子滤波器芯片;2023 年,悉尼大学 EGGLETON B J

课题组通过将包含调制器和探测器的硅光芯片与非线性 As_2S_3 光波导进行异质集成,报道了带宽仅为 37 MHz 的可调谐微波光子带阻滤波器^[48],如图 13(b)所示;SOI 材料平台具有 CMOS 工艺兼容、集成度高以及光电单片集成的优势,自 2018 年加拿大渥太华大学姚建平课题组首次通过单片集成相位调制器、高 Q 值微盘滤波器和光电探测器,报道了可调谐微波光子带通滤波器以来^[49],一些硅基微波光子滤波器芯片相继报道^[33-36]。2021 年,北京大学王兴军课题组 SOI 平台上,通过单片集成一个双驱动 MZ 调制器、一个高品质因子微环和一个光电探测器,并将该 SOI 芯片与一个 InP 半导体激光器芯片进行端面耦合,构建了可调谐的微波光子带通滤波器^[33],如图 13(c)所示;另外,InP 作为唯一支持有源/无源全单片集成的材料平台,可以实现激光器、调制器、滤波器和探测器的单片集成,从而构建全集成的微波光子滤波器芯片^[50],如图 13(d)所示。但是,由于其较高的制作成本、较高的损耗等不足,报道相对较少。

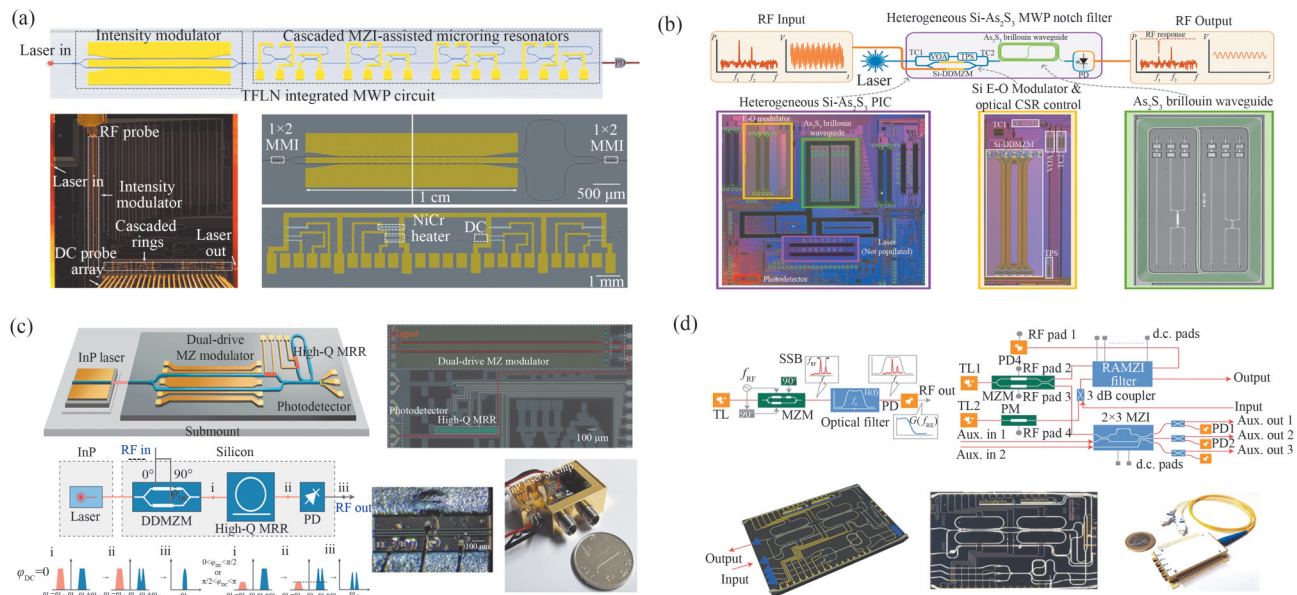


图 13 高集成微波光子滤波器芯片。(a)基于 TFLN 平台^[21]; (b)基于 As_2S_3 /SOI 混合集成^[48]; (c)基于 SOI 平台^[33]; (d)基于 InP 平台^[50]

Fig. 13 Highly integrated microwave photonic filter chips. (a) Based on TFLN platform^[21]; (b) Based on As_2S_3 /SOI hybrid integration^[48]; (c) Based on SOI platform^[33]; (d) Based on InP platform^[50]

基于集成器件的相干型微波光子滤波器对比如表 2 所示。可以看出该类微波光子滤波器主要采用相位调制器 (Phase Modulator, PM)、马赫-曾德调制器 (Mach-Zehnder Modulator, MZM)、双驱动马赫-曾德调制器 (Dual-Drive Mach-Zehnder Modulator, DDMZM) 以及双平行马赫-曾德调制器 (Dual-Parallel Mach-Zehnder Modulator, DPMZM) 对激光载波进行相位调制、强度调制以及非平衡双边带调制等,然后借助于微环/微盘、微球、光子晶体 (Photonic Crystal, PhC) 微腔、 As_2S_3 波导 SBS 等光学滤波器对该调制光信号的光边带和载波进行幅/相调控,最后将处理后的光载波和光边带在光电探测器上拍频,实现带通/带阻微波光子滤波响应。得益于 As_2S_3 波导 SBS 效应的超窄带损耗/增益谱,其可以实现带宽窄至 20 MHz 的高频谱分辨率微波光子滤波,但其具有带宽调谐难、需要额外光泵浦源的不足,且无法实现光源、调制器、探测器的单片集成,必须通过多材料体系的混合集成;对于氮化硅平台,其超低波导传输损耗可以实现高 Q 值的微环/微盘,从而可以实现带宽低至百 MHz 量级的微波光子滤波,但也无法支持光源、调制器、探测器的单片集成;对于薄膜铌酸锂 (Thin Film Lithium Niobate, TFLN) 材料平台,可以实现微波光子滤波器中调制器和微环的单片集成,但由于铌酸锂波导传输损耗相对较高,因此微波光子滤波器的带宽还处于 GHz 左右;对于 SOI 平台,由于其可以实现调制器、光滤波器、光电探测器的单片集成,且具备 CMOS 工艺兼容的优点,因此在集成微波光子滤波器领域研究最多,一些单片集成 (除光源) 的高集成度微波光子滤波器相继报道。虽然其波导传输损耗高,但是通过制作工艺和波导优化设计也可以实现带宽低至 20 MHz 左右的高频率分辨率滤波。

表2 基于集成器件的相干型微波光子滤波器性能
Table 2 Performance of coherent microwave photonic filter based on integrated components

Microwave photonic filter scheme	Filter type	Filter bandwidth/GHz	Frequency tuning range/GHz	Suppression ratio/dB
Discrete DPMZM+ single Si ₃ N ₄ all-pass micro-ring ^[16]	Band-stop	0.247~0.84	2~8	>60
Discrete DDMZM + single Si ₃ N ₄ all-pass micro-ring ^[17]	Band-stop	0.65 ~ 2.2	2.5~18.75	>50
Discrete MZM + dual Si ₃ N ₄ all-pass micro-rings ^[18]	Band-stop	0.15~0.35	1~12	>50
Discrete PM +SOI micro-ring assisted cascaded MZI ^[20]	Band-stop	0.78	4~36	>60
Discrete MZM+ single Si ₃ N ₄ Add-Drop micro-ring ^[22]	Band-pass	0.42	1 ~ 40	44
Discrete OSSB+ SOI 4-order CROW ^[23]	Band-pass	0.24~1.76	4~36	32~42
Discrete PM+ single SOI all-pass micro-ring ^[24]	Band-pass	0.17	2~18.4	26.5
Discrete PM+ single SOI all-pass micro-ring ^[25]	Band-pass	0.026	3.4~19.3	26.5
Discrete PM+ SOI single all-pass micro-disk ^[26]	Band-pass	0.103	1~30	22.3
Discrete PM/DPMZM+ single SOI all-pass micro-disk ^[27]	Band-pass/ Band-stop	0.063/0.061	0.4~15.7/0.1~16.3	37.5/52.1
Discrete PM+ dual SOI all-pass micro-rings ^[28]	Band-pass	1.65	6~17	20
Discrete PM+ dual Si ₃ N ₄ all-pass micro-rings ^[29]	Band-pass	0.38~15.74	4~21.5	34
Discrete PM+ cascaded four Si ₃ N ₄ all-pass micro-rings ^[30]	Band-pass	3~7	0.3~25	30
Discrete PM+ cascaded six Si ₃ N ₄ all-pass micro-rings ^[31]	Band-pass	2.1~3.5	5.8~18.2	32
Discrete PM+ dual SOI all-pass micro-rings ^[32]	Band-pass	0.84~1.8	2~8	20
Discrete PM+ SBS in As ₂ S ₃ waveguide ^[38]	Band-pass	0.02~0.04	2~12	20
Discrete DPMZM+ SBS in As ₂ S ₃ waveguide ^[39]	Band-pass	0.033~0.088	1~30	55
Discrete PM+ SBS in As ₂ S ₃ waveguide ^[40]	Band-pass	0.03~0.44	3~30	20
Discrete PM+ PhC nanocavity ^[42]	Band-stop	0.06	12.9~32.3	>60
Discrete DPMZM+ SiO ₂ microsphere ^[43]	Band-stop	0.015	1.5~9.5	>55
Discrete MZM+ suspended SOI waveguide ^[45]	Band-pass	0.005	/	~40
TFLN on-chip MZM+ dual all-pass micro-rings ^[21]	Band-stop	1.3	1.5 ~ 21.5	>60
TFLN on-chip PM+ dual all-pass micro-rings ^[46]	Band-pass	0.7~3	2~62	21~25
TFLN on-chip MZM+ cascaded micro-rings ^[47]	Band-pass/ Band-stop	1.6/1.6	2.6~31.5/2.6~35.4	10~25/7.8
SOI on-chip DDMZM+ single all-pass micro-ring + PD ^[33]	Band-pass/ Band-stop	0.36~0.47/0.38~0.45	3~21/3~25	10/40
SOI on-chip PM+ cascaded micro-rings + PD ^[34]	Band-pass/ Band-stop	0.25~2.07/0.36~0.53	3~24/5~30	18/50
SOI on-chip DDMZM+ cascaded all-pass micro-rings + PD ^[35]	Band-pass/ Band-stop	0.15~3/0.15~2	2~40/2~40	20~35

3 总结与展望

可以看出,经十余年的发展,集成微波光子滤波器已经取得了很好的研究进展。在构成微波光子滤波器的核心单元器件方面,依托 SOI、 Si_3N_4 、TFLN、InP 等材料平台,研制出了一系列高性能的激光器芯片、调制器芯片、光电探测器芯片、滤波器芯片等;在滤波器链路架构与性能优化方面,提出了射频抑制增强、相位-强度转换、频谱响应整形等有效手段;在系统集成度方面,从采用光学信号处理芯片和其他分立的激光器、调制器、探测器构建微波光子滤波器,逐渐向片上集成调制器、滤波器、光电探测器甚至电驱动控制的高集成化方向发展。但是,要实现更高集成度、更高性能的集成微波光子芯片,还存在以下关键技术挑战:1)通常光学滤波器的带宽和 FSR 存在矛盾,因此如何通过优化滤波器结构同时实现高频率分辨率(减小滤波带宽)和大频率调谐范围是难点之一,目前只能同时实现带宽几十 MHz 和 $\text{FSR} \approx 100 \text{ GHz}$ (对应频率调谐范围 $\sim 50 \text{ GHz}$),未来需要拓展至 MHz 量级带宽和百 GHz 以上的频率调谐范围,满足更大工作频率范围的超精细频谱分辨需求;2)相比传统微波滤波器约 1~3 dB 的损耗噪声系数,受限於光电光转换效率,集成微波光子滤波器的损耗和噪声系数分别通常高达 $\sim 25 \text{ dB}$ 和 $\sim 35 \text{ dB}$,虽然可以采用光放大改善,但目前片上光放大技术还不成熟,因此实现低损耗、低噪声系数的集成微波光子滤波器极具挑战;3)相比传统微波滤波器 1.2~1.5 的形状因子和 40~50 dB 的带外抑制,集成微波光子滤波器的滤波频谱形状因子和射频带外抑制通常只有 3 和 20~30 dB,尽管通过器件级联可以进行改善,但是会带来损耗和控制难度增大的问题,因此也是需要解决的问题之一;4)集成微波光子滤波器的稳定性受到光载波频率以及环境因素的影响,尤其是其频率稳定性通常为 GHz 量级,通过开发其自动稳定与控制系统可以实现几十 MHz 量级的频率稳定性^[51, 52],但是亟需进一步降低至亚 MHz 量级;5)基本的集成微波光子滤波器通常由激光器、调制器、滤波器、探测器等多个器件构成,而这些器件的最优性能通常需要在不同的材料平台上实现,目前绝大部分报道都还在单个材料平台上实现部分器件的单片集成,基于多材料平台混合集成的微波光子滤波器还鲜有报道,因此高效、稳定的异质异构集成技术是亟需解决的关键技术;6)受限於材料、结构等因素,目前集成微波光子滤波器通常只能实现部分高性能的指标(如超窄带宽、高射频抑制等、宽频率调谐范围、大带宽调谐范围等),还无法实现整体性能的综合优化,如何突破这些指标之间的相互制约也是难点之一;7)集成微波光子芯片的光电封装技术目前还面临封装后的带宽恶化、射频串扰、热管理难等问题,也是其实用化、工程化应用的关键。

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Research Progresses of Integrated Microwave Photonic Filters (Invited)

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Abstract: A Microwave Photonic Filter (MPF) is a device that filters microwave signals by first modulating them into the optical domain, then processing them using optoelectronic components. Compared to traditional electronic microwave filters, they exhibit advantages such as superior frequency tuning range, flexible spectrum reconfiguration, and inherent immunity to electromagnetic interference, etc. These benefits make MPFs highly promising for widespread applications in wireless communication, radar, and electronic warfare systems. With the advancement of integrated optoelectronic technologies, MPFs are progressively evolving from discrete fiber-optic devices towards integrated solutions. This transition aims to substantially reduce their size, weight, power consumption, and cost. In this review, firstly the system architectures and working principles of both incoherent and coherent integrated MPFs are presented. Subsequently, recent research advances in these two categories of MPFs are reviewed.

For incoherent integrated MPFs, multi-tap configurations are typically adopted, utilizing Finite Impulse Response (FIR) digital filter architectures rooted in discrete signal processing algorithms. Some

key integrated optical components enabling dispersion-delayed sampling in multi-tap MPFs are given, such as integrated high-dispersion chips, multi-wavelength light sources, and spectral shaping chips. By adopting these functional chips into microwave photonic filter links, some MPFs with good frequency tuning capabilities and out-of-band RF suppression have been reported. But the limited number of taps and unattainable complex tap coefficients resulting in insufficient spectral reconstruction capability of the achieved incoherent MPFs. To date, only aforementioned integrated chips have been integrated into microwave photonic filter links, while other critical components still rely on discrete fiber-based devices. Incoherent MPFs with higher integration levels remain unreported in the literature.

For coherent integrated MPF, typically microwave signals are modulated onto a single-wavelength laser source, where various integrated optical filters are adopted to spectrally shape modulated optical signal, followed by down-conversion at a photodetector to convert optical domain filtering response into microwave domain. Various integrated optical components to construct coherent MPFs such as Micro-Ring Resonator (MRR)/Micro-Disk Resonator (MDR), nonlinear As₂S₃ waveguide with Stimulated Brillouin Scattering (SBS), photonic crystal cavity, microsphere, phase shifted waveguide Bragg grating, Surface Acoustic Wave (SAW) based on suspended waveguide have been reviewed. Based on these integrated optical components, various MPF link architectures to realized band-stop and band-pass MPFs have been introduced. Band-stop MPFs can be realized through optical-to-microwave mapping based on Optical Single Sideband (OSSB) modulation. Furthermore, by employing Radio Frequency (RF) cancellation techniques via Unbalanced Optical Double Sideband (UODSB) modulation, this approach can overcome the limitation imposed by optical filter's extinction ratio on RF suppression performance and enables band-stop MPF with RF rejection ratio larger than 60 dB. On the other hand, Band-pass MPFs can be realized through either by optical carrier separation and re-entry techniques enabling direct one-to-one mapping of optical band-pass responses to the microwave domain, or phase-to-intensity conversion schemes that transform optical band-stop filtering into microwave band-pass responses. In addition, some technologies to enhance MPF's frequency resolution have been introduced, such as improving quality factors of MRR/MDR with mode manipulation, incorporating on-chip narrow-band SBS gain/loss spectra, adopting SiO₂ microsphere, etc. Up to date, frequency resolution down to about ten MHz have been demonstrated for band-pass and band-stop MPFs. Building on recent advances in integrated optical filters for MPF links, this work further surveys highly integrated microwave photonic filter chips implemented on Thin-Film Lithium Niobate (TFLN), Silicon-On-Insulator (SOI), and indium phosphide (InP) platforms, providing a comparative analysis of their respective advantages and limitations.

Finally, quantitative comparative analysis of key performance metrics of the reported incoherent and coherent integrated MPFs have been given. Some key technical challenges in integrated MPFs, including the trade-offs between filter's bandwidth and frequency tuning range, insufficient noise figure/out-of-band RF rejection ratio/frequency stability, immature heterogeneous integration, and broadband photonic packaging solution with low crosstalk and high RF integrity. Moreover, an outlook on the future development trends of integrated MPF is presented.

Key words: Microwave photonics; Optoelectronic integration; Microwave photonic filter; Coherent filter; Incoherent filter

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